S A Gabriel

List of Publications by Year
in descending order

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34	217	8	13
papers	citations	h-index	g-index
		1163117	1125743

35	35	35	187
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	SRAM-Based PUF Reliability Prediction Using Cell-Imbalance Characterization in the State Space Diagram. Electronics (Switzerland), 2022, 11, 135.	3.1	1
2	Estimation during Design Phases of Suitable SRAM Cells for PUF Applications Using Separatrix and Mismatch Metrics. Electronics (Switzerland), 2021, 10, 1479.	3.1	3
3	Single Event Upsets characterization of 65â€¯nm CMOS 6T and 8T SRAM cells for ground level environment. Microelectronics Reliability, 2020, 110, 113696.	1.7	2
4	Transistor Width Effect on the Power Supply Voltage Dependence of Î±-SER in CMOS 6T SRAM. IEEE Transactions on Nuclear Science, 2020, 67, 811-817.	2.0	2
5	Selection of SRAM Cells to improve Reliable PUF implementation using Cell Mismatch Metric. , 2020, , .		1
6	Weak and Strong SRAM cells analysis in embedded memories for PUF applications. , 2019, , .		5
7	A 65-nm Reliable 6T CMOS SRAM Cell with Minimum Size Transistors. IEEE Transactions on Emerging Topics in Computing, 2019, 7, 447-455.	4.6	23
8	Design Issues for NEM-Relay-Based SRAM Devices. MATEC Web of Conferences, 2018, 210, 01005.	0.2	0
9	Evaluation of SRAM cell write margin metrics for lifetime monitoring of BTI-induced Vth drift. , 2017, , .		1
10	Cantilever NEMS relay-based SRAM devices for enhanced reliability. , 2017, , .		0
11	Statistical characterization and modeling of random telegraph noise effects in 65nm SRAMs cells. , 2017, , .		1
12	Soft error rate comparison of 6T and 8T SRAM ICs using mono-energetic proton and neutron irradiation sources. Microelectronics Reliability, 2017, 78, 38-45.	1.7	18
13	6T CMOS SRAMs reliability monitoring through stability measurements. , 2017, , .		0
14	An affordable experimental technique for SRAM write margin characterization for nanometer CMOS technologies. Microelectronics Reliability, 2016, 65, 280-288.	1.7	4
15	On-line write margin estimator to monitor performance degradation in SRAM cores. , 2016, , .		13
16	Memory State Transient Analysis (MSTA): A New Soft Error Rate Measurement Method for CMOS Memory Elements Based on Stochastic Analysis. IEEE Transactions on Nuclear Science, 2015, 62, 3353-3361.	2.0	1
17	Detailed 8-transistor SRAM cell analysis for improved alpha particle radiation hardening in nanometer technologies. Solid-State Electronics, 2015, 111, 104-110.	1.4	10
18	Radiation effects in nanometric SRAMs induced by 18 MeV protons. , 2015, , .		0

#	Article	IF	Citations
19	SRAM write margin cell estimation using wordline modulation and read/write operations. , 2014, , .		2
20	An Experimental Approach to Accurate Alpha-SER Modeling and Optimization Through Design Parameters in 6T SRAM Cells for Deep-Nanometer CMOS. IEEE Transactions on Device and Materials Reliability, 2014, 14, 1013-1021.	2.0	16
21	Adaptive static and dynamic noise margin improvement in minimum-sized 6T-SRAM cells. Microelectronics Reliability, 2014, 54, 2613-2620.	1.7	21
22	SRAM Alpha-SER Estimation From Word-Line Voltage Margin Measurements: Design Architecture and Experimental Results. IEEE Transactions on Nuclear Science, 2014, 61, 1849-1855.	2.0	8
23	Top-side pulsed laser induced single event upsets in highly-scaled SRAM devices. , 2013, , .		1
24	Accurate alpha soft error rate evaluation in SRAM memories. , 2013, , .		1
25	Alpha-SER determination from word-line voltage margin (WVM) measurements: Design architecture and experimental results. , 2013, , .		0
26	Pass-transistors pMOS based 8T SRAM cell for layout compaction. , 2011, , .		5
27	8T vs. 6T SRAM cell radiation robustness: A comparative analysis. Microelectronics Reliability, 2011, 51, 350-359.	1.7	20
28	Static and dynamic stability improvement strategies for 6T CMOS low-power SRAMs. , 2010, , .		13
29	Design Hardening of Nanometer SRAMs Through Transistor Width Modulation and Multi-Vt Combination. IEEE Transactions on Circuits and Systems II: Express Briefs, 2010, 57, 280-284.	3.0	17
30	Cross-BIC architecture for single and multiple SEU detection enhancement in SRAM memories. , 2010, , .		3
31	A CMOS integrated system for SEE-induced transients acquisition. , 2009, , .		0
32	Analysis of radiation-hardening techniques for 6T SRAMs with structured layouts. Reliability Physics Symposium, 2009 IEEE International, 2009, , .	0.0	6
33	Critical charge characterization in 6-T SRAMs during read mode. , 2009, , .		13
34	Analysis of current transients in SRAM memories for single event upset detection. , 2009, , .		2